

## **Data Sheet**

## Features

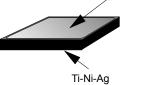
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Oxide Passivated Junction Very Low Forward Voltage 125 ° C Junction Operating Low Reverse Leakage Supplied as Wafers Chromium Barrier >1000V ESD (MM)

Cr-Al-Ni-Ag - Suffix "Ag"





Electrical Characteristics @ 25°c	Symbol	Unit	SB039C040-0.5-W-Ag (See <u>ordering code</u> below)
Maximum Repetitive Reverse Voltage (2)	V <sub>RRM</sub>	Volt	40
Maximum Forward Voltage @ I <sub>F</sub> = 0.5A (1)(2)	V <sub>F</sub>	Volt	0.36
Typical Average Forward Rectified Current (2)	I <sub>F(AV)</sub>	Amp	0.5
Reverse Leakage Current @ $V_R$ = 40V (2)	I <sub>R(1)</sub>	μA	500
Reverse Leakage Current @ $V_R$ = 40V, 125°C (2)	I <sub>R(2)</sub>	mA	15
ESD Machine Model (MM)	V <sub>ESD(mm)</sub>	Volt	>1000
Junction Operating Temperature Range (2)	TJ	°C	-45 to +125
Storage Temperature Range (2)	T <sub>SG</sub>	°C	-45 to +125

(1) Pulse Width tp =  $< 300\mu$ S, Duty Cycle < 2%

(2) The characteristics above assume the die are assembled in industry standard packages using appropriate attach methods.

